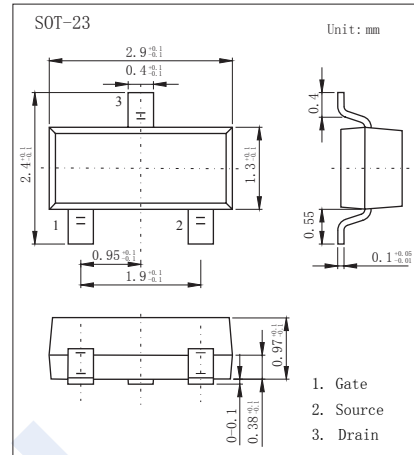
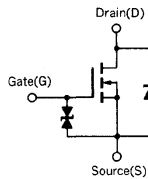


N-Channel MOSFET

2SK1582

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 0.2 A$
- $R_{DS(ON)} < 5 \Omega$ ($V_{GS} = 4V$)
- $R_{DS(ON)} < 3 \Omega$ ($V_{GS} = 10V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	200	mA
Pulsed Drain Current (Note.1)	I_{DM}	400	
Power Dissipation $T_a = 25^\circ C$	P_D	200	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = 250 \mu A$, $V_{GS} = 0V$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V$, $V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 20V$			± 1	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 5V$, $I_D = 1 \mu A$	0.8		1.8	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4V$, $I_D = 10m A$			5	Ω
		$V_{GS} = 10V$, $I_D = 10m A$			3	
Forward Transconductance	g_{FS}	$V_{DS} = 5V$, $I_D = 10m A$	20	60		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 5V$, $f = 1MHz$		28		pF
Output Capacitance	C_{oss}			30		
Reverse Transfer Capacitance	C_{rss}			7		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = 5V$, $V_{DS} = 5V$, $I_D = 10mA$, $R_L = 500 \Omega$, $R_G = 10 \Omega$		55		ns
Turn-On Rise Time	t_r			200		
Turn-Off DelayTime	$t_{d(off)}$			180		
Turn-Off Fall Time	t_f			250		

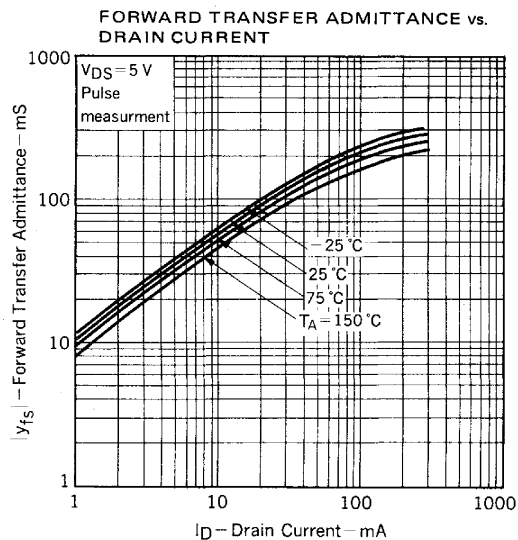
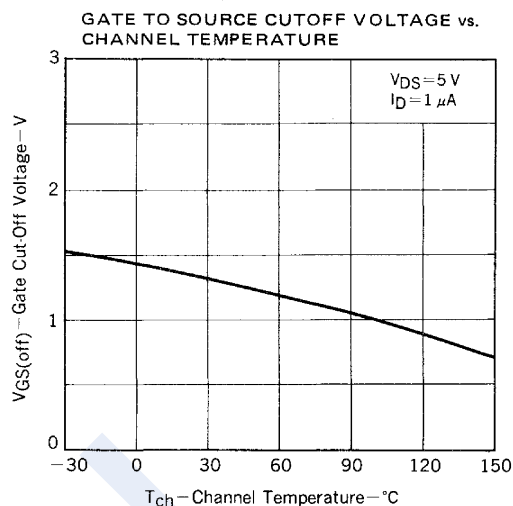
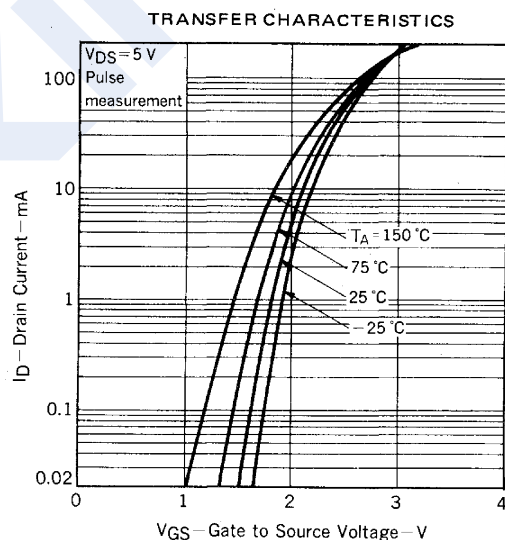
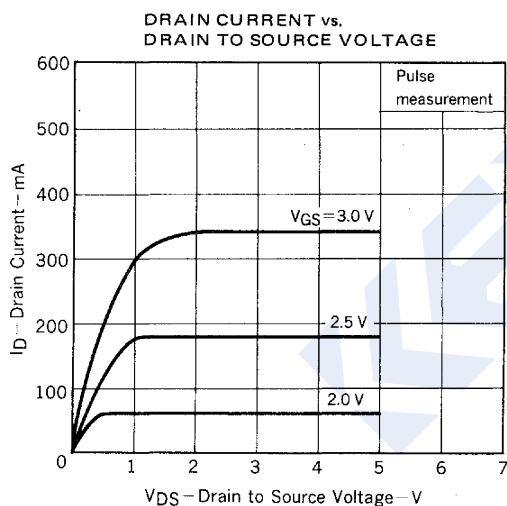
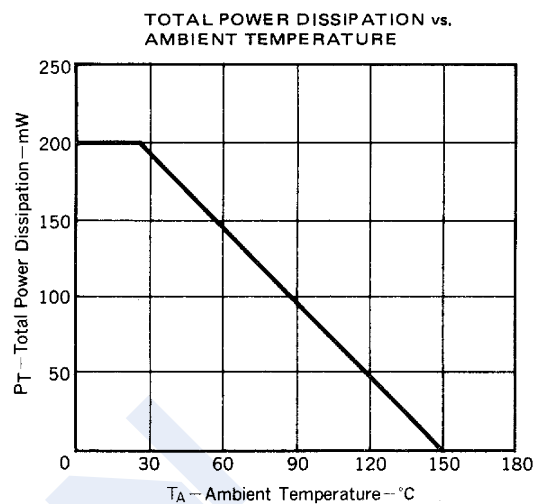
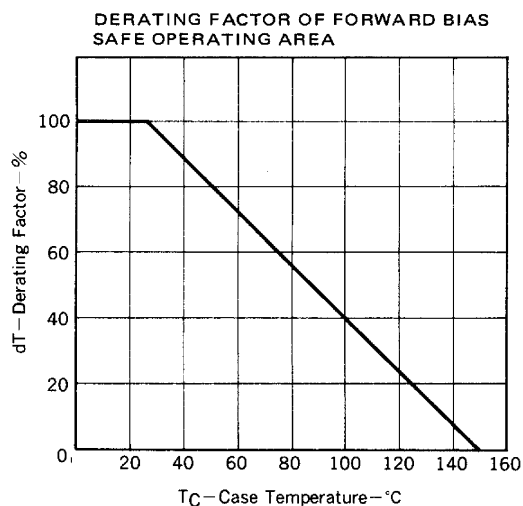
■ Marking

Marking	G15
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N-Channel MOSFET

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Typical Characteristics



N-Channel MOSFET

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■ Typical Characteristics

